

JiÅÃ- Oswald

List of Publications by Year in descending order

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1147
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#	ARTICLE	IF	CITATIONS
1	Near-infrared photoluminescence properties of Er/Yb- and Ho/Yb-doped multicomponent silicate glass " The role of GeO ₂ , Al ₂ O ₃ and ZnO. Journal of Non-Crystalline Solids, 2022, 582, 121457.	3.1	9
2	Near-infrared photoluminescence enhancement and radiative energy transfer in RE-doped zinc-silicate glass (RE=Ho, Er, Tm) after silver ion exchange. Journal of Non-Crystalline Solids, 2021, 557, 120580.	3.1	19
3	Er implantation into various cuts of ZnO " experimental study and DFT modelling. Journal of Alloys and Compounds, 2020, 816, 152455.	5.5	12
4	1.5 µm photoluminescence and upconversion photoluminescence in GeGaAsS:Er chalcogenide glass. Pure and Applied Chemistry, 2019, 91, 1757-1767.	1.9	4
5	Damage accumulation and implanted Gd and Au position in a- and c-plane GaN. Thin Solid Films, 2019, 680, 102-113.	1.8	9
6	Strong suppression of In desorption from InGaN QW by improved technology of upper InGaN/GaN QW interface. Journal of Crystal Growth, 2019, 507, 310-315.	1.5	3
7	Co-implantation of Er and Yb ions into single-crystalline and nano-crystalline diamond. Surface and Interface Analysis, 2018, 50, 1218-1223.	1.8	7
8	InGaN/GaN Structures: Effect of the Quantum Well Number on the Cathodoluminescent Properties. Physica Status Solidi (B): Basic Research, 2018, 255, 1700464.	1.5	6
9	Photoluminescence in pulsed-laser deposited GeGaSbS:Er films. Optical Materials, 2018, 85, 246-253.	3.6	1
10	Erbium Luminescence Centres in Single- and Nano-Crystalline Diamond " Effects of Ion Implantation Fluence and Thermal Annealing. Micromachines, 2018, 9, 316.	2.9	5
11	Water-soluble polymers as chelating agents for the deposition of Er ³⁺ /Yb ³⁺ :LiNbO ₃ waveguiding films. Journal of Sol-Gel Science and Technology, 2018, 86, 274-284.	2.4	3
12	1.2 µm and 1.5 µm near-infrared photoluminescence and visible upconversion photoluminescence in GeGaS:Er ³⁺ /Ho ³⁺ glasses under 980nm excitation. Journal of Materials Science: Materials in Electronics, 2018, 29, 17314-17322.	2.2	4
13	Erbium ion implantation into diamond " measurement and modelling of the crystal structure. Physical Chemistry Chemical Physics, 2017, 19, 6233-6245.	2.8	18
14	GaAsSb-capped InAs QD type-II solar cell structures " improvement by composition profiling of layers surrounding QD. Materials Research Express, 2017, 4, 025502.	1.6	0
15	Comparison of MOVPE grown GaAs, InGaAs and GaAsSb covering layers for different InAs/GaAs quantum dot applications. Journal of Crystal Growth, 2017, 464, 59-63.	1.5	5
16	The influence of silver ion exchange on the luminescence properties of Er-Yb silicate glasses. Optical Materials, 2017, 72, 183-189.	3.6	15
17	Physico-chemical and optical properties of Er ³⁺ -doped and Er ³⁺ /Yb ³⁺ -co-doped Ge ₂₅ Ga _{9.5} Sb _{0.5} S ₆₅ chalcogenide glass. Pure and Applied Chemistry, 2017, 89, 429-436.	1.9	7
18	Ageing of PVP/LiNbO ₃ solutions and its impact on the optical properties of Er ³⁺ /Yb ³⁺ :LiNbO ₃ waveguiding films. Journal of Physics and Chemistry of Solids, 2017, 111, 343-348.	4.0	3

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19	Solution-processed Er ³⁺ -doped As ₂ S ₃ chalcogenide films: optical properties and 1.5 μm photoluminescence activated by thermal treatment. Journal of Materials Chemistry C, 2017, 5, 8489-8497.	5.5	10
20	GaAsSb/InAs/(In)GaAs type II quantum dots for solar cell applications. Journal of Crystal Growth, 2017, 464, 64-68.	1.5	12
21	Modification of Er:YbAG film microstructure with a sintering agent. IOP Conference Series: Materials Science and Engineering, 2017, 266, 012004.	0.6	0
22	Polyethylene glycol (PEG) used in the preparation of (Er ³⁺ /Yb ³⁺):LiNbO ₃ waveguides. IOP Conference Series: Materials Science and Engineering, 2017, 266, 012011.	0.6	0
23	Photoluminescence of InGaN/GaN MQW structures – technological aspects. , 2016, , .		0
24	GaAsSb/InAs QDs structures for advanced telecom lasers. , 2016, , .		0
25	Thin films of ErNbO ₄ and YbNbO ₄ prepared by sol-gel. Journal of Sol-Gel Science and Technology, 2016, 78, 600-605.	2.4	5
26	Sol-gel-derived planar waveguides of Er ³⁺ :Yb ₃ Al ₅ O ₁₂ prepared by a polyvinylpyrrolidone-based method. Journal of Sol-Gel Science and Technology, 2016, 80, 531-537.	2.4	6
27	Waveguiding Er ³⁺ /Yb ³⁺ :LiNbO ₃ films prepared by a sol-gel method using polyvinylpyrrolidone. Journal of Luminescence, 2016, 176, 260-265.	3.1	11
28	Growth and properties of the MOVPE GaAs/InAs/GaAsSb quantum dot structures. Physica B: Condensed Matter, 2016, 480, 14-22.	2.7	3
29	Optical waveguides in Er:LiNbO ₃ fabricated by different techniques – A comparison. Optical Materials, 2016, 53, 160-168.	3.6	8
30	The influence of silver-ion doping using ion implantation on the luminescence properties of Er ³⁺ :Yb silicate glasses. Nuclear Instruments & Methods in Physics Research B, 2016, 371, 350-354.	1.4	11
31	Erbium-ion implantation into various crystallographic cuts of Al ₂ O ₃ . Nuclear Instruments & Methods in Physics Research B, 2015, 365, 89-93.	1.4	3
32	MOVPE prepared InAs/GaAs quantum dots covered by GaAsSb layer with long wavelength emission at 1.8 μm. Journal of Crystal Growth, 2015, 414, 167-171.	1.5	9
33	Growth of InAs/GaAs quantum dots covered by GaAsSb in multiple structures studied by reflectance anisotropy spectroscopy. Journal of Crystal Growth, 2015, 414, 156-160.	1.5	16
34	Electrochemical properties of corrosion products formed on Zn-Mg, Zn-Al and Zn-Al-Mg coatings in model atmospheric conditions. Materials and Corrosion - Werkstoffe Und Korrosion, 2015, 66, 777-782.	1.5	43
35	Influence of gallium on infrared luminescence in Er ³⁺ -doped Yb ₃ Al ₅ O ₁₂ films grown by the liquid phase epitaxy. Journal of Luminescence, 2015, 164, 90-93.	3.1	8
36	Two-band superlinear electroluminescence in GaSb based nanoheterostructures with AlSb/InAs _x Sb _{1-x} deep quantum well. Journal of Applied Physics, 2014, 115, 223102.	2.5	2

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37	The structural changes and optical properties of LiNbO3 after Er implantation using high ion fluencies. Nuclear Instruments & Methods in Physics Research B, 2014, 332, 74-79.	1.4	7
38	Effect of the lower and upper interfaces on the quality of InAs/GaAs quantum dots. Applied Surface Science, 2014, 301, 173-177.	6.1	10
39	Green, red and near-infrared photon up-conversion in Ga ⁺ Ge ⁺ Sb ⁺ S:Er ³⁺ amorphous chalcogenides. Journal of Luminescence, 2014, 147, 209-215.	3.1	17
40	Infrared luminescence in Er ³⁺ :Yb ³⁺ Al ₅ O ₁₂ bulk ceramics prepared by sol-gel method. Journal of the European Ceramic Society, 2014, 34, 3779-3782.	5.7	12
41	Ytterbium and erbium derivatives of 2-methoxyethanol and their use in the thin film deposition of Er-doped Yb ₃ Al ₅ O ₁₂ . Journal of Sol-Gel Science and Technology, 2014, 70, 142-148.	2.4	9
42	Graded GaAsSb strain reducing layers covering InAs/GaAs quantum dots. Journal of Crystal Growth, 2013, 370, 303-306.	1.5	19
43	Type I-type II band alignment of a GaAsSb/InAs/GaAs quantum dot heterostructure influenced by dot size and strain-reducing layer composition. Journal Physics D: Applied Physics, 2013, 46, 095103.	2.8	26
44	Electric field-assisted erbium doping of LiNbO3 from melt. Scripta Materialia, 2013, 68, 739-742.	5.2	2
45	Light emitting diodes with InAs/GaAsSb self-assembled quantum dot layer embedded in GaAs. Thin Solid Films, 2013, 543, 83-87.	1.8	0
46	Erbium diffusion from erbium metal or erbium oxide layers deposited on the surface of various LiNbO3 cuts. Optical Materials, 2013, 36, 402-407.	3.6	2
47	Preparation and physical properties of luminescent 80GeSe ₂ ·(20-x)Sb ₂ Se ₃ ·xSb ₂ Te _y :Pr ₂ Se ₃ glasses; x=0, 1, 3, 10; y=2, 3, 4. Journal of Luminescence, 2013, 134, 558-565.	3.1	3
48	Optical properties of laser-prepared Er- and Er,Yb-doped LiNbO3 waveguiding layers. Laser Physics, 2013, 23, 105819.	1.2	13
49	Combined vertically correlated InAs and GaAsSb quantum dots separated by triangular GaAsSb barrier. Journal of Applied Physics, 2013, 114, 174305.	2.5	8
50	Optical properties of Bi-doped epoxy novolak resin containing Ce, Dy, and Y ions. Journal of Applied Polymer Science, 2012, 125, 710-715.	2.6	0
51	Erbium ion implantation into different crystallographic cuts of lithium niobate. Optical Materials, 2012, 34, 652-659.	3.6	11
52	Intense near-infrared and midinfrared luminescence from the Dy ³⁺ -doped GeSe ₂ ·Ga ₂ Se ₃ ·MI (M=K, Cs,) Tj ETQ, 0 0 0 rgBT /Overlo 2.5 29	2.5	29
53	Self-Assembled InAs/GaAs Quantum Dots Covered by Different Strain Reducing Layers Exhibiting Strong Photo- and Electroluminescence in 1.3 and 1.55 μm Bands. Journal of Nanoscience and Nanotechnology, 2011, 11, 6804-6809.	0.9	8
54	A Numerical Study Of Magneto Transport In 2D Electronic Systems In The Presence Of Non-Uniform Magnetic Fields. , 2011, , .		0

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55	InAs/GaAs quantum dot capping in kinetically limited MOVPE growth regime. Journal of Crystal Growth, 2011, 317, 39-42.	1.5	2
56	Influence of strain reducing layers on electroluminescence and photoluminescence of InAs/GaAs QD structures. Journal of Crystal Growth, 2011, 315, 110-113.	1.5	12
57	Quantum confinement in MOVPE-grown structures with self-assembled InAs/GaAs quantum dots. Journal of Physics: Conference Series, 2010, 245, 012079.	0.4	0
58	InGaAs and GaAsSb strain reducing layers covering InAs/GaAs quantum dots. Journal of Crystal Growth, 2010, 312, 1383-1387.	1.5	17
59	Gate Controlled Separation of Edge and Bulk Current Transport in the Quantum Hall Effect Regime. Journal of Low Temperature Physics, 2010, 159, 180-183.	1.4	2
60	Properties of epoxy novolak resin layers doped with bismuth for photoluminescence near 1300 nm. Journal of Applied Polymer Science, 2010, 117, 1608-1612.	2.6	2
61	Spectroscopic properties of Ni ²⁺ and rare-earth codoped Ge ⁴⁺ Ga ⁴⁺ Sb ⁴⁺ S glass. Journal of Physics and Chemistry of Solids, 2010, 71, 30-34.	4.0	7
62	Surface processes during growth of InAs/GaAs quantum dot structures monitored by reflectance anisotropy spectroscopy. Surface Science, 2010, 604, 318-321.	1.9	22
63	Electro- and photoluminescence of InAs/GaAs quantum dot structures. Journal of Physics: Conference Series, 2010, 245, 012080.	0.4	0
64	Bismuth(III) doped polymer layers for telecommunication applications. , 2009, , .		0
65	InAs/GaAs quantum dot structures emitting in the 1.55 μ m band. IOP Conference Series: Materials Science and Engineering, 2009, 6, 012007.	0.6	3
66	Influence of capping layer thickness on electronic states in self assembled MOVPE grown InAs quantum dots in GaAs. Superlattices and Microstructures, 2009, 46, 324-327.	3.1	12
67	Er ³⁺ medium energy ion implantation into lithium niobate. Nuclear Instruments & Methods in Physics Research B, 2009, 267, 1332-1335.	1.4	6
68	Diffusion process applied in fabrication of ion-exchanged optical waveguides in novel Er ³⁺ and Er ³⁺ /Yb ³⁺ -doped silicate glasses. Journal of Materials Science: Materials in Electronics, 2009, 20, 510-513.	2.2	5
69	Optical properties of PMMA doped with erbium(III) and ytterbium(III) complexes. Polymer Engineering and Science, 2009, 49, 1814-1817.	3.1	6
70	Ultrafast photoluminescence spectroscopy of InAs/GaAs quantum dots. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 853-856.	0.8	4
71	Chromium(IV) ions containing novel silicate glasses. Optical Materials, 2009, 32, 85-88.	3.6	1
72	Dysprosium (III)-doped novel silicate glasses. Optical Materials, 2009, 32, 79-84.	3.6	0

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73	Highly oriented crystalline Er:YAG and Er:YAP layers prepared by PLD and annealing. Applied Surface Science, 2009, 255, 5292-5294.	6.1	3
74	Structure and optical properties of chalcogenide glasses doped with Pr ³⁺ and Yb ³⁺ ions. Journal of Non-Crystalline Solids, 2009, 355, 1865-1868.	3.1	6
75	InAs/GaAs quantum dot structures covered by InGaAs strain reducing layer characterized by photomodulated reflectance. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2008, 147, 175-178.	3.5	7
76	Growth and properties of InAs/In _x Ga _{1-x} As/GaAs quantum dot structures. Journal of Crystal Growth, 2008, 310, 2229-2233.	1.5	16
77	Influence of capping layer on the properties of MOVPE-grown InAs/GaAs quantum dots. Journal of Crystal Growth, 2008, 310, 5081-5084.	1.5	7
78	Near and mid-infrared luminescence of new chalcogenide glasses doped with Pr ³⁺ ions. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2008, 146, 107-109.	3.5	15
79	Optical characterisation of MOVPE grown vertically correlated InAs/GaAs quantum dots. Microelectronics Journal, 2008, 39, 1070-1074.	2.0	18
80	Investigation of GaN layers doped with Er ³⁺ and Er ³⁺ + Yb ³⁺ ions using the transmittance measurement. , 2008, , .		0
81	Optical properties of Dy ³⁺ -doped epoxy novolak resin. , 2008, , .		1
82	Optical properties of PMMA polymer doped with Er ³⁺ and Er ³⁺ /Yb ³⁺ ions. Journal of Physics: Conference Series, 2008, 100, 012021.	0.4	1
83	CIRCUIT TYPE SIMULATIONS OF MAGNETO-TRANSPORT IN THE QUANTUM HALL EFFECT REGIME. International Journal of Modern Physics B, 2007, 21, 1424-1428.	2.0	6
84	Substrate temperature changes during molecular beam epitaxy growth of GaMnAs. Journal of Applied Physics, 2007, 102, .	2.5	12
85	Photoluminescence and magnetophotoluminescence of vertically stacked InAs/GaAs quantum dot structures. Physica E: Low-Dimensional Systems and Nanostructures, 2007, 36, 106-113.	2.7	14
86	Ag ⁺ planar waveguides in novel Er ³⁺ -Yb ³⁺ silicate glasses. Journal of Physics and Chemistry of Solids, 2007, 68, 1263-1267.	4.0	4
87	Lateral shape of InAs/GaAs quantum dots in vertically correlated structures. Journal of Crystal Growth, 2007, 298, 570-573.	1.5	9
88	Properties of MOVPE InAs/GaAs quantum dots overgrown by InGaAs. Journal of Crystal Growth, 2007, 298, 582-585.	1.5	25
89	Porous glass doping by Er ³⁺ for photonics applications. Journal of Materials Science: Materials in Electronics, 2007, 18, 379-382.	2.2	0
90	Localised doping of Li-silicate glasses by Er ³⁺ ion exchange to fabricate thin optical layers. Optical Materials, 2007, 29, 753-759.	3.6	1

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91	Erbium doping into silicate glasses to form luminescent optical layers for photonics applications. Journal of Physics and Chemistry of Solids, 2007, 68, 891-895.	4.0	3
92	<title>Rare earth doped gallium nitride layers for photonics applications</title>. , 2006, 6180, 260.		0
93	Optical properties of Er ³⁺ + Yb ³⁺ -doped gallium nitride layers. , 2006, , .		0
94	1.3 Åµm emission from InAs/GaAs quantum dots. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 3811-3814.	0.8	8
95	Photoluminescence and magnetophotoluminescence of circular and elliptical InAs/GaAs quantum dots. Materials Science and Engineering C, 2006, 26, 983-986.	7.3	9
96	Elongation of InAs-GaAs quantum dots from magnetophotoluminescence measurements. Applied Physics Letters, 2006, 89, 153108.	3.3	10
97	GaSb based lasers operating near 2.3¼m for high resolution absorption spectroscopy. Spectrochimica Acta - Part A: Molecular and Biomolecular Spectroscopy, 2005, 61, 3066-3069.	3.9	16
98	Effect of hydrogen passivation on polycrystalline silicon thin films. Thin Solid Films, 2005, 487, 152-156.	1.8	30
99	Room-temperature diode laser photoacoustic spectroscopy near 2.3¼m. Applied Physics B: Lasers and Optics, 2005, 81, 857-861.	2.2	12
100	Electroluminescence of type II broken-gap p-Ga _{0.84} In _{0.16} As _{0.22} Sb _{0.78} -p-InAs heterostructures with a high-mobility electron channel at the interface. Journal of Applied Physics, 2005, 98, 083512.	2.5	1
101	Properties of Er ³⁺ doped layers grown from Er: YAG (YAP) crystalline targets by sub-picosecond laser deposition. Laser Physics Letters, 2004, 1, 248-252.	1.4	3
102	Effect of divalent cations on properties of Er ³⁺ -doped silicate glasses. Optical Materials, 2004, 27, 331-336.	3.6	39
103	InAs Å-layer structures in GaAs grown by MOVPE and characterised by luminescence and photocurrent spectroscopy. Journal of Crystal Growth, 2003, 248, 328-332.	1.5	5
104	Dynamical behaviour of the Å-doped Au/GaAs Schottky barrier. Physica Status Solidi A, 2003, 195, 61-66.	1.7	0
105	Erbium Medium Temperature Localised Doping into Lithium Niobate and Sapphire: A Comparative Study. Solid State Phenomena, 2003, 90-91, 559-564.	0.3	0
106	Erbium localized doping into various cuts of lithium niobate and sapphire: a comparative study. , 2003, , .		0
107	Photovoltage spectroscopy of InAs/GaAs quantum dot structures. Journal of Applied Physics, 2002, 91, 10103.	2.5	20
108	<title>Nd-doped KGW crystalline waveguides fabricated by pulsed laser deposition</title>. , 2002, , .		0

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109	Influence of pulse duration and annealing on crystallinity and luminescence of laser-deposited Er-doped YAG (YAP) layers. , 2002, , .		0
110	Magneto-photoluminescence study of electronic transitions in InAs/GaAs quantum dot layers. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 88, 247-251.	3.5	3
111	Lasers with $\hat{\Gamma}$ InAs layers in GaAs. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 88, 312-316.	3.5	3
112	Photoluminescence of Ga _{0.94} In _{0.06} As _{0.13} Sb _{0.87} solid solution lattice matched to InAs. Optical Materials, 2002, 19, 455-459.	3.6	6
113	Polarization anisotropy of photoluminescence from multilayer InAs/GaAs quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 13, 229-232.	2.7	9
114	Low temperature photoluminescence of Ga _{0.84} In _{0.16} As _{0.22} Sb _{0.78} solid solutions lattice matched to InAs. Journal of Applied Physics, 2001, 90, 2813-2817.	2.5	10
115	MBE growth of InAs/InAsSb/AlAsSb structures for mid-infrared lasers. Journal of Crystal Growth, 2001, 223, 341-348.	1.5	9
116	InAs/GaAs multiple quantum dot structures grown by LP-MOVPE. Thin Solid Films, 2000, 380, 101-104.	1.8	6
117	InAs/GaAs lasers with very thin active layer. Thin Solid Films, 2000, 380, 233-236.	1.8	6
118	Magneto-photoluminescence study of energy levels of self-organised InAs/GaAs quantum dots. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2000, 69-70, 318-323.	3.5	8
119	Optical properties of low-phonon-energy Ge ₃₀ Ga ₅ Se ₆₅ :Dy ₂ Se ₃ chalcogenide glasses. Journal of Physics and Chemistry of Solids, 2000, 61, 1583-1589.	4.0	32
120	Study of single and double Si $\hat{\Gamma}$ -doped GaAs layers by spectral photoconductivity measurements. Thin Solid Films, 1999, 342, 262-265.	1.8	4
121	Strained In _x Ga _{1-x} As/GaAs multiple quantum wells grown by MOVPE. European Physical Journal D, 1999, 49, 805-811.	0.4	0
122	Electroluminescence and photoelectric properties of type II broken-gap n-In(Ga)As(Sb)/N-GaSb heterostructures. Journal of Applied Physics, 1999, 86, 6264-6268.	2.5	8
123	Synthesis and optical properties of the Ge $\hat{\Gamma}$ -Sb $\hat{\Gamma}$ -S:PrCl ₃ glass system. Journal of Non-Crystalline Solids, 1999, 256-257, 266-270.	3.1	47
124	Planar waveguide lasers and structures created by laser ablation $\hat{\Gamma}$ an overview. European Physical Journal D, 1998, 48, 577-597.	0.4	23
125	Synthesis and properties of Ge-Sb-S: NdCl ₃ glasses. Semiconductors, 1998, 32, 812-816.	0.5	16
126	Growth of active Nd-doped YAP thin-film waveguides by laser ablation. Applied Physics A: Materials Science and Processing, 1998, 66, 583-586.	2.3	13

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127	Study of InAs quantum dots in GaAs prepared on misoriented substrates. Thin Solid Films, 1998, 336, 80-83.	1.8	12
128	Direct experimental observation of the Hall angle in the low-temperature breakdown regime of n ⁺ GaAs. Physical Review B, 1998, 58, 13099-13102.	3.2	8
129	Synthesis and properties of GeS ₂ -Ga ₂ S ₃ :NdCl ₃ and GeS ₂ -Ga ₂ S ₃ :Nd ₂ O ₃ glasses. Journal of Non-Crystalline Solids, 1997, 213-214, 58-62.	3.1	12
130	Novel exciton-like optical transitions in AlGaAs/GaAs single heterojunctions. Journal of Luminescence, 1997, 72-74, 898-900.	3.1	1
131	Characterisation of InP and GaInAsP layers prepared by liquid-phase epitaxy using holmium doping and gettering. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1997, 44, 160-163.	3.5	8
132	Photoconductivity of porous silicon in contact with a liquid electrolyte. Thin Solid Films, 1997, 297, 64-67.	1.8	3
133	Dependence of PS photoluminescence on relative humidity. Thin Solid Films, 1996, 276, 268-271.	1.8	6
134	The influence of preparation conditions on the photoluminescence spectra of light-emitting Si prepared by laser pulse irradiation of a-Si:H. Thin Solid Films, 1996, 276, 306-309.	1.8	2
135	Charge transport in porous silicon: considerations for achievement of efficient electroluminescence. Thin Solid Films, 1996, 276, 187-190.	1.8	21
136	Synthesis and physical properties of the system (GeS ₂) _{80-x} (Ga ₂ S ₃) _{20-x} Pr glasses. Optical Materials, 1996, 6, 217-223.	3.6	29
137	Meander Type LPE and High Temperature Stability of Elastically Strained GaInAsP/InP Layers. , 1996, , 61-64.		0
138	Photoluminescence from OH-related radiative centres in silica, metal oxides and oxidized nanocrystalline and porous silicon. Journal of Luminescence, 1995, 63, 279-287.	3.1	57
139	Photoconductivity study of self-supporting porous silicon. Thin Solid Films, 1995, 255, 269-271.	1.8	22
140	Preparation of periodic structures by meander type liquid phase epitaxy. Journal of Crystal Growth, 1995, 146, 287-292.	1.5	6
141	Urbach edges in light-emitting porous silicon and related materials. Thin Solid Films, 1995, 255, 234-237.	1.8	21
142	Light-emitting Si prepared by laser annealing of a-Si:H. Thin Solid Films, 1995, 255, 302-304.	1.8	3
143	Photoelectric properties of self-supporting porous silicon. Applied Physics Letters, 1994, 64, 3118-3120.	3.3	23
144	Formation of luminescent silicon by laser annealing of a-Si:H. Applied Physics Letters, 1994, 64, 2555-2556.	3.3	17

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145	On the stability of single $\hat{\Gamma}$ -layer in GaAs. Solid State Communications, 1994, 89, 925-928.	1.9	2
146	Temperature behaviour of luminescence of free-standing porous silicon. Solid State Communications, 1994, 89, 297-300.	1.9	5
147	Origin of recombination transitions at the lattice-matched GaInAsSb/GaSb n-type heterojunctions. Journal of Applied Physics, 1994, 75, 4189-4193.	2.5	4
148	The luminescence behaviour of porous silicon layers. Solid State Communications, 1993, 85, 347-350.	1.9	10
149	Transport properties of self-supporting porous silicon. Journal of Non-Crystalline Solids, 1993, 164-166, 961-964.	3.1	20
150	Spectroscopic study of Si-related defects in nonhomogeneous GaAs: Si. Materials Letters, 1993, 17, 237-240.	2.6	0
151	Impurity avalanche breakdown in n-type InP layers. Semiconductor Science and Technology, 1993, 8, 112-115.	2.0	5
152	Impurity breakdown and electric-field-dependent luminescence in MBE and VPE GaAs layers. Semiconductor Science and Technology, 1992, 7, 203-209.	2.0	20
153	Gettering properties of PrO ₂ in In _{0.53} Ga _{0.47} As LPE growth. Journal of Crystal Growth, 1991, 110, 862-866.	1.5	21
154	Switching of Impurity Breakdown in n-type GaAs by FIR or Near Edge Illumination. Physica Status Solidi (B): Basic Research, 1991, 167, K43.	1.5	3
155	Inhomogeneities in n-Type and Semi-Insulating InP Crystals Studied by Photoluminescence Topography and Raman Scattering. Physica Status Solidi A, 1991, 126, 493-500.	1.7	2
156	The photoluminescence spectra of thin Si-doped GaAs layers grown by MBE. Physica Status Solidi A, 1990, 118, 567-576.	1.7	2
157	Electro-optical properties of InGaAs layers grown by hydride vapour phase epitaxy. Crystal Research and Technology, 1990, 25, 25-30.	1.3	0
158	Si related defects in GaAs. Infrared Physics, 1989, 29, 725-727.	0.5	1
159	Lateral Distribution of Si-Related Defects and Carrier Density in GaAs Crystals. Physica Status Solidi A, 1989, 111, 345-360.	1.7	5
160	Heavy doping with Sn of GaAs layers grown by molecular beam epitaxy for non-alloyed ohmic contacts. European Physical Journal D, 1988, 38, 224-230.	0.4	3
161	Luminescence of Pr, Nd and Yb ions implanted in GaAs and GaP. European Physical Journal D, 1988, 38, 1288-1293.	0.4	8
162	The electric field dependence of photoconductivity spectra in AlGaAs/GaAs DH laser diodes in relation with laser parameters. Physica Status Solidi A, 1986, 97, 657-665.	1.7	1

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163	Impurity incorporation and structural defects in hydride VPE InP films. Journal of Crystal Growth, 1986, 79, 386-393.	1.5	2
164	Spatial Distribution of Point Defects and Complexes in Semi-Insulating LEC and Si-Doped GF Grown GaAs Crystals. Materials Science Forum, 1986, 10-12, 1235-1240.	0.3	2
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